FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))	Attorney Docket No.: Z&PINFN10455 Appl. No. Applicant JOSEF BOECK Filing Date January 22, 2002 Group Art Unit

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	3,974,516	8/10/76	Steinmaier			
	B	5,213,988	5/25/93	Yamauchi et al.			
	C	5,747,374	5/5/98	Jeon			
	D						
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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	TRANSL. NO
RP	J	58 155 764	9/16/83	Japan				
RP	K	59 006 574	1/13/84	Japan				
	L							
	M							
	N							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP		Kameyama, S. et al.: "Base Link-Up Process Technology for Self-Aligned Double Diffusion Bipolar Transistors", IEEE, 1987, pp. 27-30;
RP		Nakamae, M.: "Recent Progress and Future Prospect for VLSI Si Biopolar Transistors", IEEE, 1987, pp. 5-6;

EXAMINER Ron Pompey	DATE CONSIDERED 5-30-03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	N							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	✓	Chen, T et al..: "An Advanced Bipolar Transistor with Self-aligned Ion-implanted Base and W/poly Emitter", IEEE, 1987, pp. 31-33;
RP	✓	Yamaguchi, T. et al.: "Process and Device Performance of a High-Speed Double Poly-Si Bipolar Technology Using Borosenic-Poly Process with Coupling-Base Implant", IEEE, Vol. 35, No. 8, August 1988, pp. 1247-1256;

EXAMINER	DATE CONSIDERED
Ken Pompey	5-30-03

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	J	Sugiyama, M. et al.: "A40GHz f_T Si Bipolar Transistor LSI Technology", IEEE, 1989, pp. 9.1.1-9.1.4;
RP	K	Van der Velden, J. et al.: "Basic: An Advanced High-Peformance Bipolar Process", IEEE, 1989, pp. 9.4.1-9.4.4;

EXAMINER Ron Pompey | DATE CONSIDERED 5-31-03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	K							
	L							
	M							
	N							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	✓	Shiba, T. et al.: "Base Peripheral Effects on High Performance Self-Aligned Bipolar Devices (SICOS)", Scripta Technica, Inc., 1990, pp. 100-105;
RP	✓	Hayden, J. D. et al.: "A New Technique for Forming a Shallow Link Base in a Double Polysilicon Bipolar Transistor", IEEE, 1994, pp. 63-68;

EXAMINER Ron Pompey	DATE CONSIDERED 5-30-03

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	/	Park, J. et al.: "Ultrashallow p^+/n Junction Formation by 0.5-1 keV Ion Implantation", Japanese Journal of Applied Physics, Vol. 37, No. 11B, 1998, pp. L1376-L1378

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